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<b>Application serial number</b>	200405408 (I289929)																												
<b>Title</b>	Semiconductor memory device and method of manufacturing the same																												
<b>Publication Date</b>	2004/04/01 (2007/11/11 )																												
<b>Application Date</b>	2003/08/29																												
<b>Application No.</b>	092124136																												
<b>IPC</b>	H01L-021/00																												
<b>Inventor</b>	KOMORI, HIDEKIJP; SHIMADA, HISAYUKIJP; SUN, YUUS; KINOSHITA, HIROYUKIJP																												
<b>Applicant</b>	FUJITSU LIMITEDJP; FASL LLCUS; ADVANCED MICRO DEVICES, INC.US																												
<b>Priority Number</b>	2002/08/30 JP20020256120																												
<b>Abstract</b>	A semiconductor memory device and a method of manufacturing the same are disclosed, wherein a drain (7) has a low concentration and shallow low concentration impurity area (7a), which is formed in conformity with a control gate (5), and a high concentration impurity area (7b), which has higher concentration and is deeper than the low concentration impurity area (7a) and is formed in conformity with a side wall film (8). As a result, the short channel effect is improved and the programming efficiency is enhanced due to the low concentration impurity area (7a), and the contact resistance within the drain (7) is decreased while providing a drain contact hole forming portion (70) upon the high concentration impurity area (7b).																												
<b>Patent Right Change</b>	<table border="0"> <tr> <td><b>Application number</b></td> <td>092124136</td> </tr> <tr> <td><b>Authorization note</b></td> <td>No</td> </tr> <tr> <td><b>Qualification right note</b></td> <td>No</td> </tr> <tr> <td><b>Transfer Note</b></td> <td>No</td> </tr> <tr> <td><b>Inheritance Note</b></td> <td>No</td> </tr> <tr> <td><b>Trust note</b></td> <td>No</td> </tr> <tr> <td><b>Objection note</b></td> <td>No</td> </tr> <tr> <td><b>Exposure Note</b></td> <td>No</td> </tr> <tr> <td><b>Invalidation date</b></td> <td></td> </tr> <tr> <td><b>Withdrawal date</b></td> <td></td> </tr> <tr> <td><b>Issue date of patent right</b></td> <td>20071111</td> </tr> <tr> <td><b>Due date of patent right</b></td> <td>20230828</td> </tr> <tr> <td><b>Due date of annual fee</b></td> <td>20081110</td> </tr> <tr> <td><b>Due year of annual fee</b></td> <td>001</td> </tr> </table>	<b>Application number</b>	092124136	<b>Authorization note</b>	No	<b>Qualification right note</b>	No	<b>Transfer Note</b>	No	<b>Inheritance Note</b>	No	<b>Trust note</b>	No	<b>Objection note</b>	No	<b>Exposure Note</b>	No	<b>Invalidation date</b>		<b>Withdrawal date</b>		<b>Issue date of patent right</b>	20071111	<b>Due date of patent right</b>	20230828	<b>Due date of annual fee</b>	20081110	<b>Due year of annual fee</b>	001
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